

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2700

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

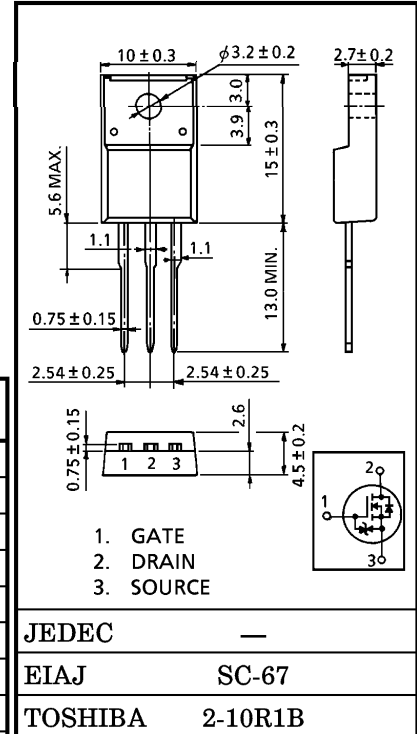
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 3.7\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 2.6S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 720V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	3	A
	Pulse	I_{DP}	9	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	295	mJ
Avalanche Current		I_{AR}	3	A
Repetitive Avalanche Energy*		E_{AR}	4	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



JEDEC —

EIAJ SC-67

TOSHIBA 2-10R1B

Weight : 1.9g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C / W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

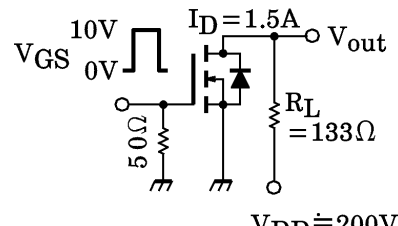
** $V_{DD} = 90V$, Starting $T_{ch} = 25^\circ C$, $L = 60.0mH$, $R_G = 25\Omega$, $I_{AR} = 3A$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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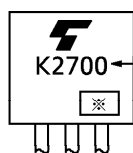
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±30V, VDS = 0V	—	—	±10	μA
Gate-Source Breakdown Voltage		V (BR) GSS	IG = ±10μA, VDS = 0V	±30	—	—	V
Drain Cut-off Current		IDSS	VDS = 720V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID = 10mA, VGS = 0V	900	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	2.0	—	4.0	V
Drain-Source ON Resistance		RDS (ON)	VGS = 10V, ID = 1.5A	—	3.7	4.3	Ω
Forward Transfer Admittance		Yfs	VDS = 20V, ID = 1.5A	0.65	2.6	—	S
Input Capacitance		Ciss	VDS = 25V, VGS = 0V, f = 1MHz	—	750	—	pF
Reverse Transfer Capacitance		Crss		—	10	—	
Output Capacitance		Coss		—	70	—	
Switching Time	Rise Time	tr	 <p>VGS 10V 0V, ID = 1.5A, VDD ≐ 200V, RL = 133Ω</p>	—	15	—	ns
	Turn-on Time	ton		—	55	—	
	Fall Time	tf		—	30	—	
	Turn-off Time	t _{off}		VIN : tr, tf < 5ns, Duty ≤ 1%, tw = 10μs	—	110	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 400V, VGS = 10V, ID = 3A	—	25	—	nC
Gate-Source Charge		Qgs		—	13	—	
Gate-Drain ("Miller") Charge		Qgd		—	12	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	3	A
Pulse Drain Reverse Current	IDRP	—	—	—	9	A
Diode Forward Voltage	VDSF	IDR = 3A, VGS = 0V	—	—	-1.9	V
Reverse Recovery Time	t _{rr}	IDR = 3A, VGS = 0V	—	1100	—	ns
Reverse Recovery Charge	Q _{rr}	dIDR / dt = 100A / μs	—	7.2	—	μC

MARKING

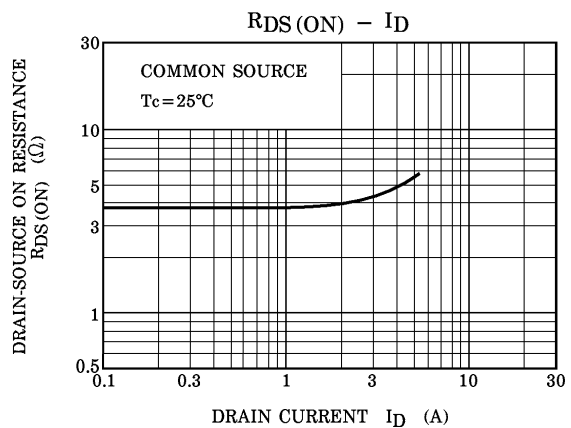
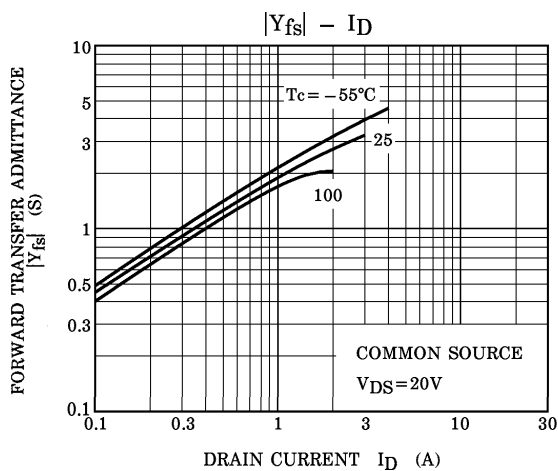
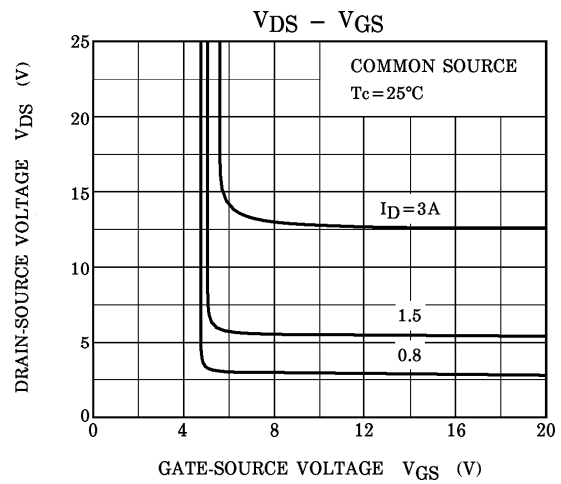
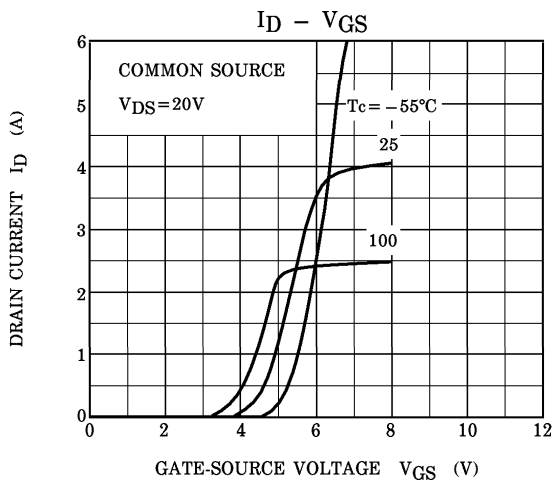
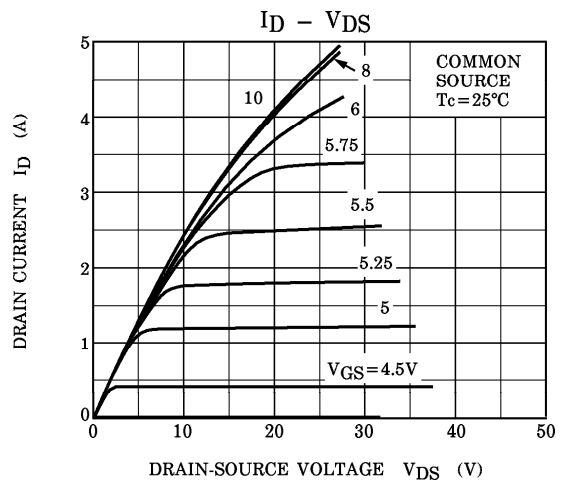
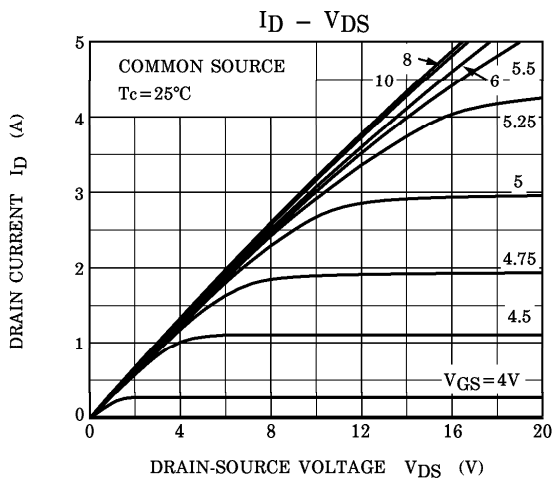


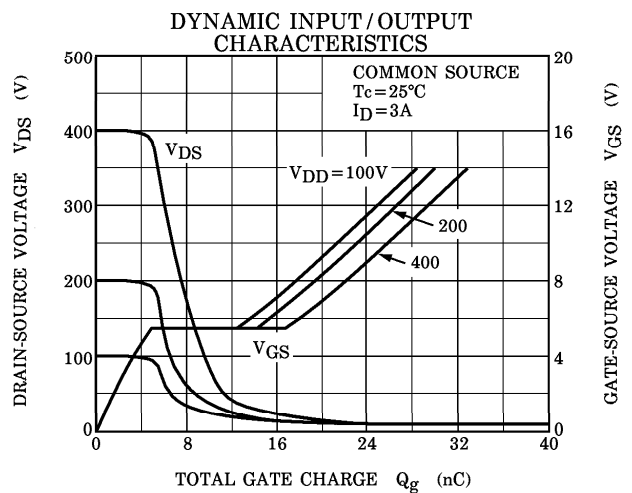
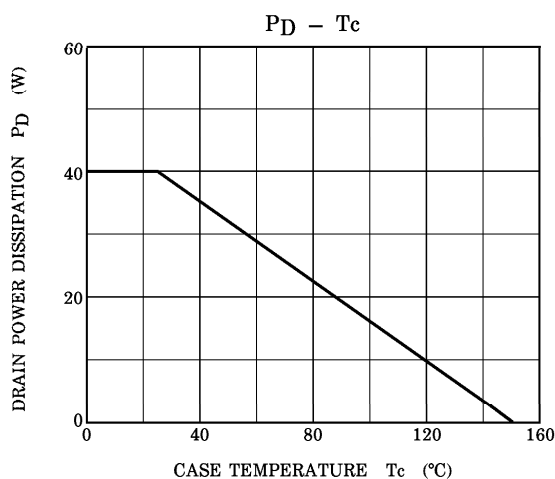
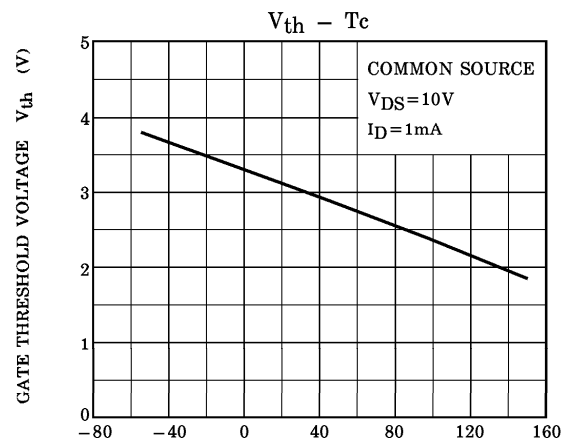
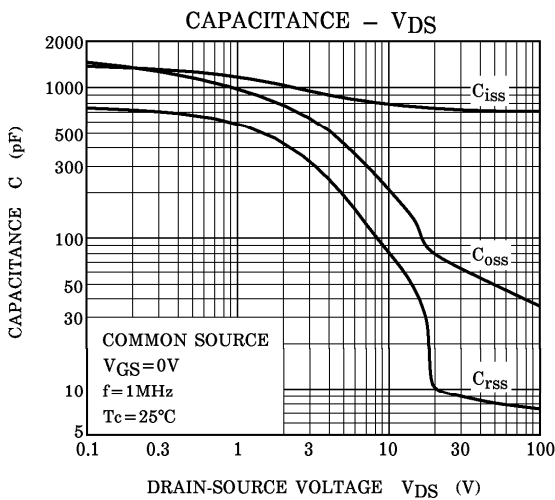
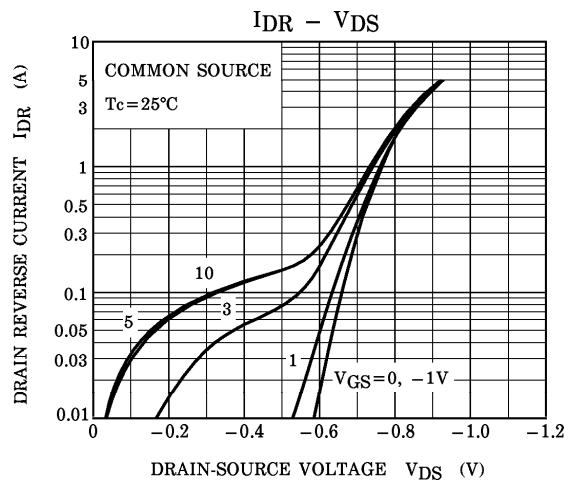
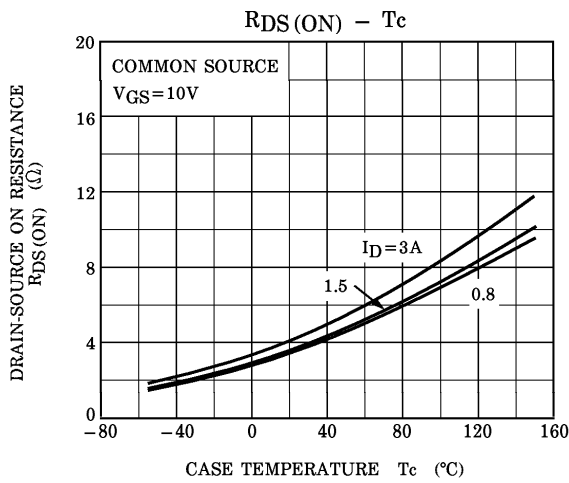
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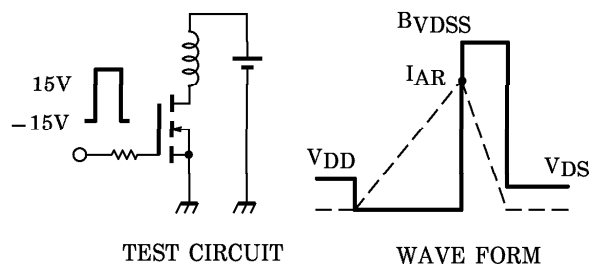
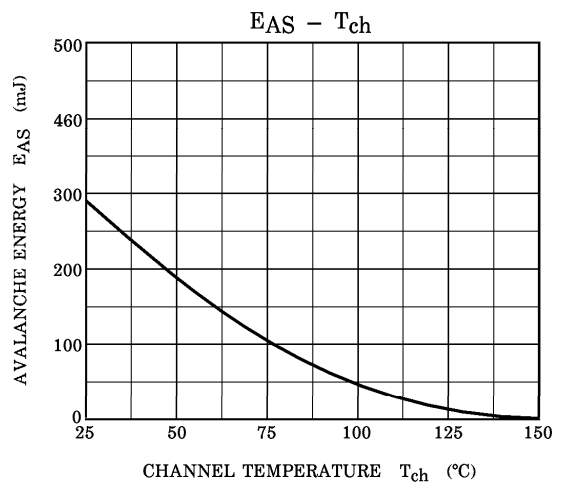
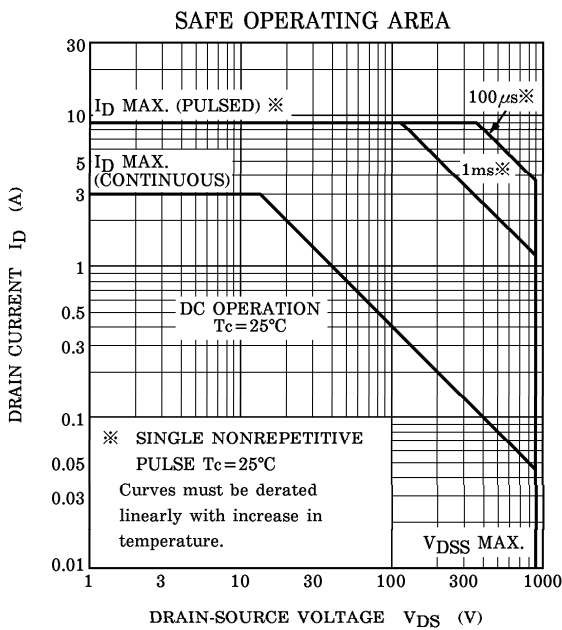
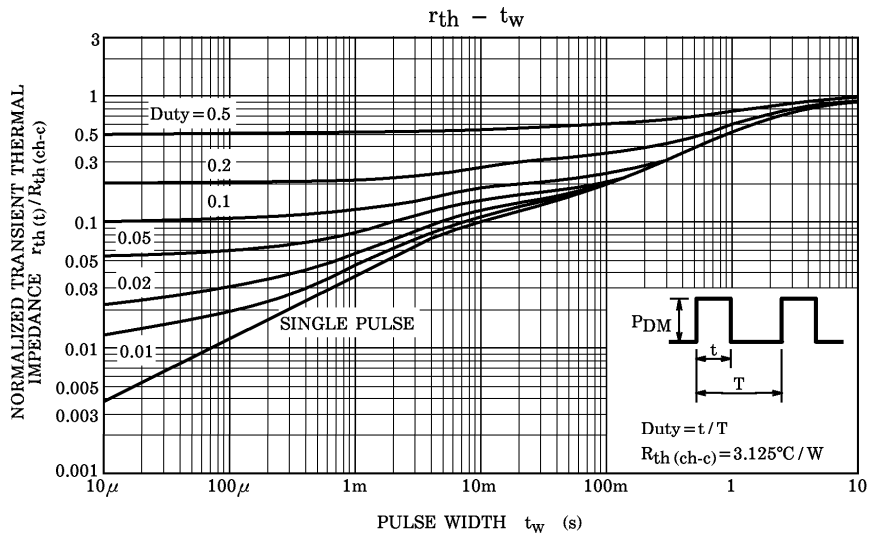
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 3A$, $R_G = 25\Omega$ $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$
 $V_{DD} = 90V$, $L = 60mH$